

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning at line 15 of page 6 with the following:

As described above, the thickness of the oxide film is determined based on the refractive index and the absorption coefficient detected by light irradiated on the oxide film. That is, the thickness of the oxide film is measured based on the change in light incident on the oxide film. Therefore, if deposits exist on the surface of the oxide film to influence the refractive index and the like, the thickness of the oxide film ~~can be measured as if it is~~ will appear to have increased according to the measurements.

Please replace the paragraph beginning at line 7 of page 9 with the following:

In a second preferred embodiment, a ~~the~~ apparent thickness of an oxide film, which has been measured ~~apparently~~, is corrected so that an accurate thickness of the oxide film is obtained. ~~An~~ The object to which the method for measuring the thickness of the oxide film is applied in the second embodiment is substantially the same as the MOS transistor in the first embodiment. The process for ~~checking product defectives~~ finding defective products based on the measured thickness of the oxide film is also substantially the same as that in the first embodiment. Mainly, the correction of the thickness is explained below.

Please replace the paragraph beginning at line 24 of page 9 with the following:

In the formula (2), "a" and "b" are constants, and "t" is an exposure period, in minutes, elapsed from the formation of the gate oxide film 8 to the measurement of the thickness. The constant a is determined by the atmosphere (temperature, moisture) around a wafer disposed

within a clean room, or the like, and was in a range of approximately 0.5 to 1.5 when it was measured in practice. The constant b is a thickness of the oxide film measured immediately after the gate oxide film 8 is formed (when $t = 1$ min).